

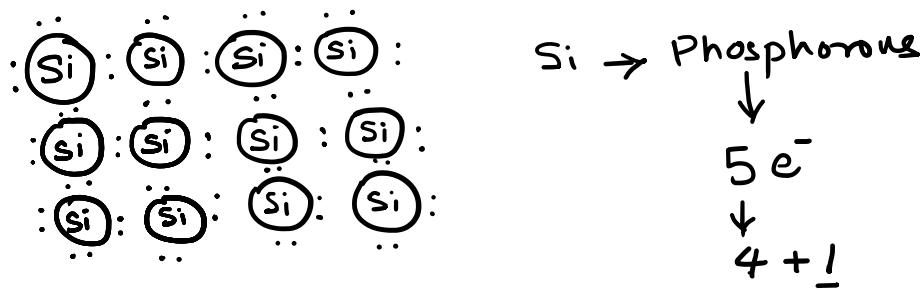
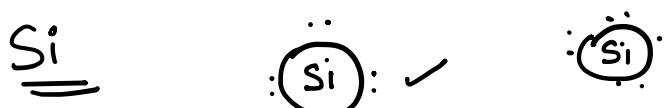
Chapter3: Semiconductor Devices and Circuits

Topics

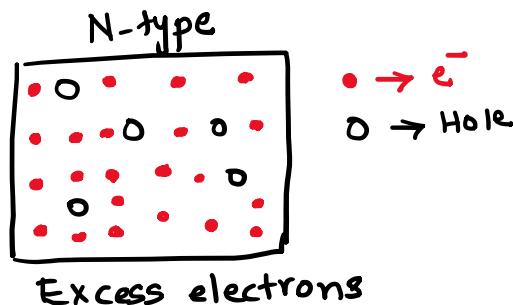
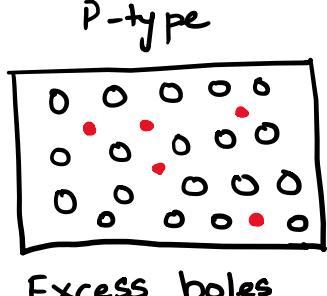
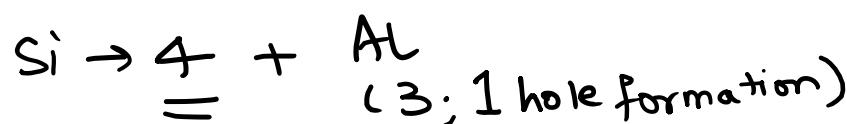
1. Working of P-N Junction Diode
2. Zener Diode
3. Diode Clipper Circuits
4. Diode Clamper Circuits
5. Half-wave and Full Wave diode rectifier
 - a. DC Output current
 - b. DC Output voltage
 - c. RMS current and Voltage
 - d. Rectifier Efficiency
 - e. Ripple factor
 - f. Peak Inverse Voltage

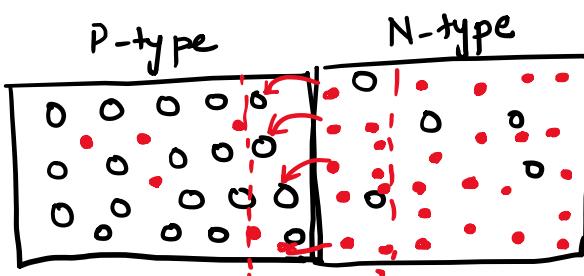
1. Working of P-N Junction Diode

Conductor. | Insulator | Semiconductor
Ge Si.

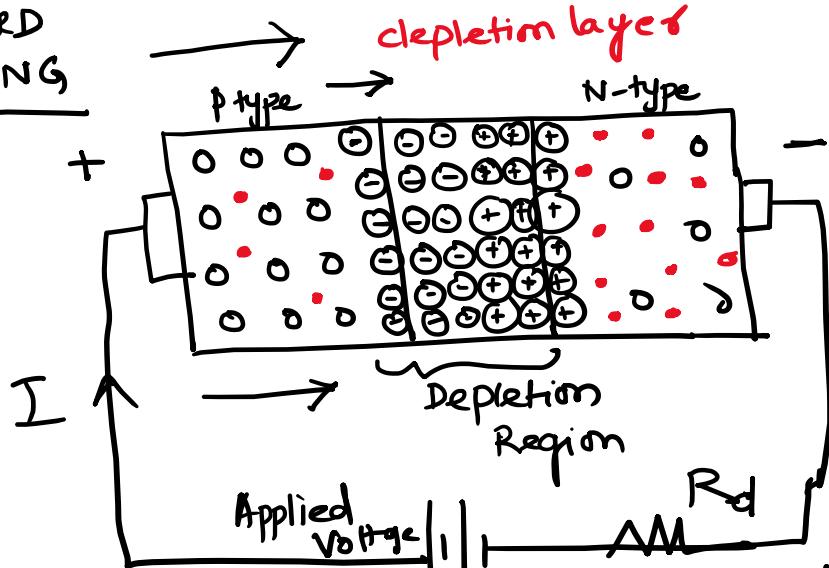


(Si is doped with Al) \rightarrow N-type doping
 (Si is doped with Al) \rightarrow 3e⁻ in his valence shell





FORWARD BIASING

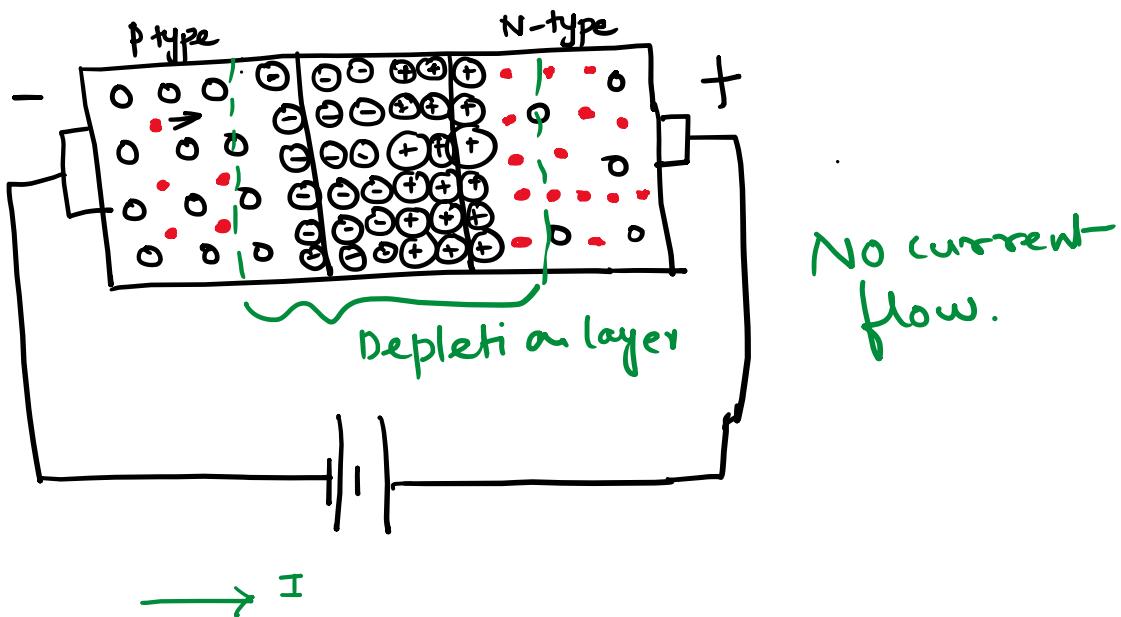


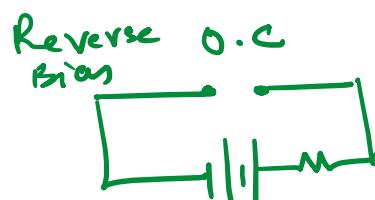
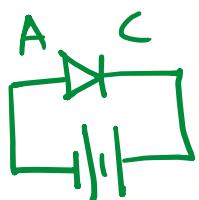
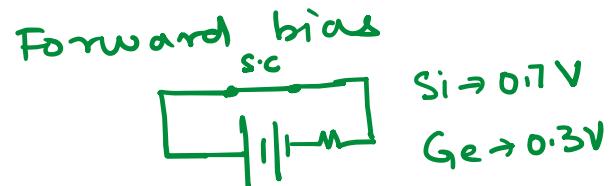
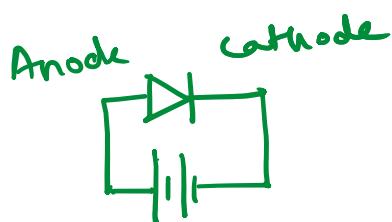
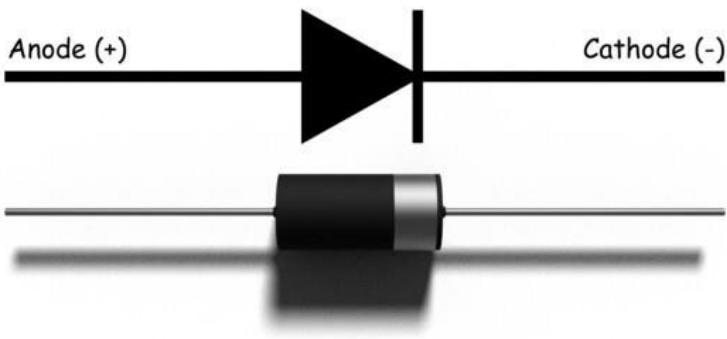
Si →
Ge →

Applied Voltage
> Barrier potential

Amount of voltage required to forward bias . : Si → 0.7V
Ge → 0.3V

REVERSE BIASING



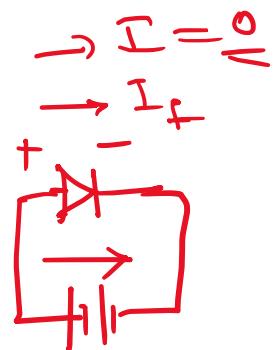
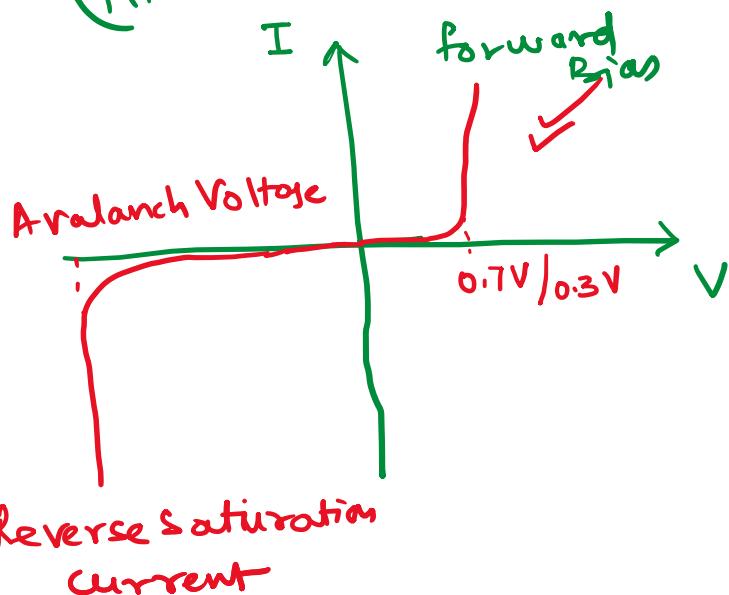


Zener diode

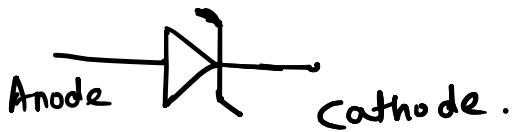
Light Emitting diode (LED)

Schottky diode

PIN diode



2. Zener Diode



Forward

Reverse

diode

$V_z = 0.6V$

Forward Bias

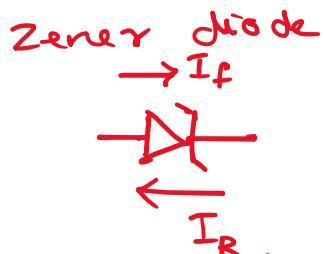
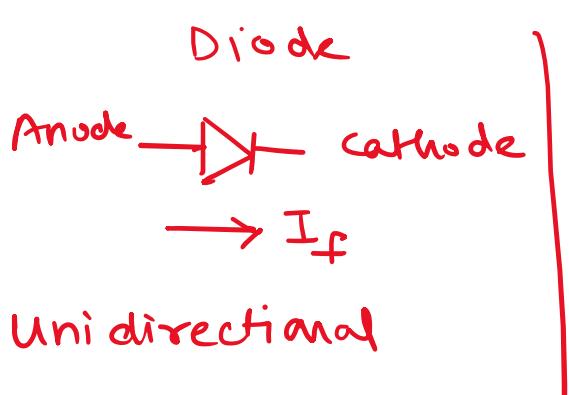
-5V, -12V

0.6V

Reverse bias ✓

Reverse Bias

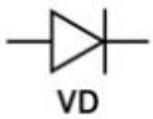
good controllable characteristics



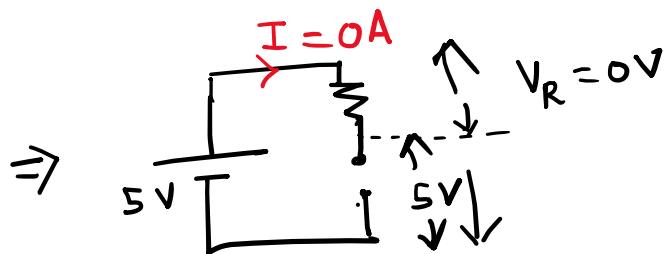
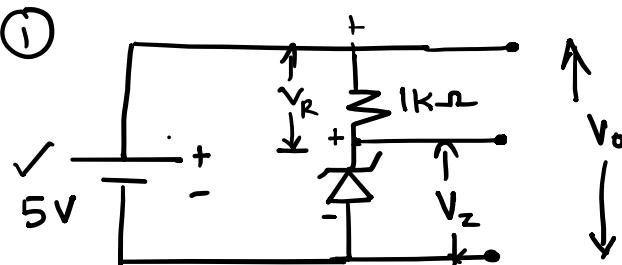
Bi-directional mode

P-N Diode & Zener diode.

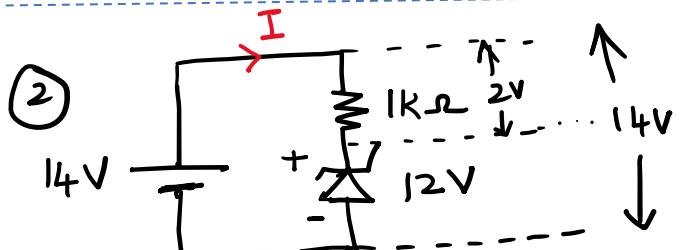
Diode Types:



Examples with Zener Diode

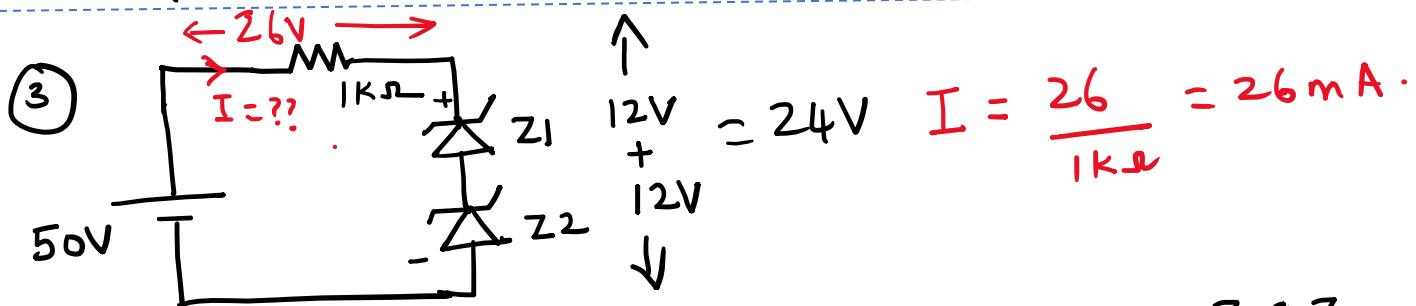


Given: Rated Reverse breakdown voltage of Zener diode = 12V



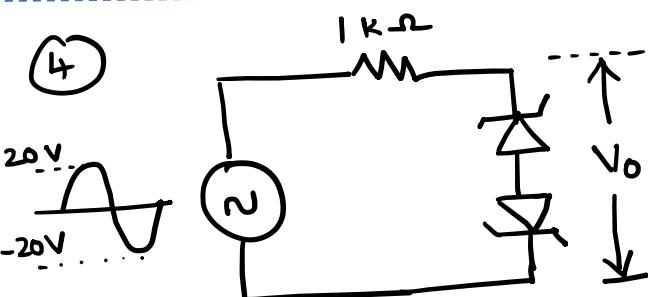
$$I = \frac{V}{R} = \frac{2}{1k\Omega} = 2mA$$

Given: $\begin{cases} 0.6V \rightarrow \text{Forward bias cond of Zener diode} \\ 12V \rightarrow \text{Reverse breakdown voltage a/c } Z_D \end{cases}$

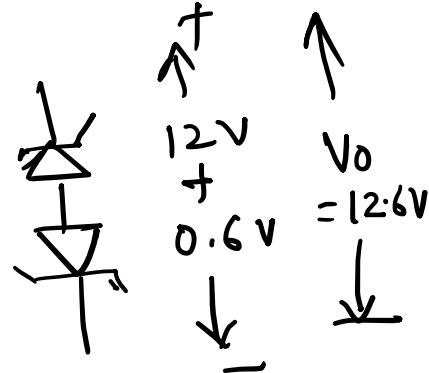
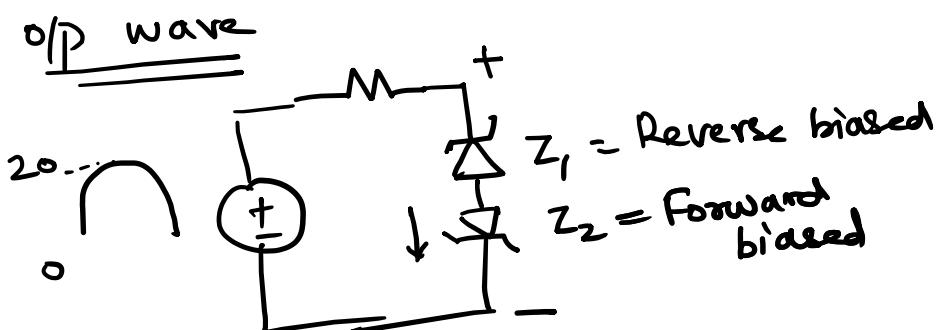


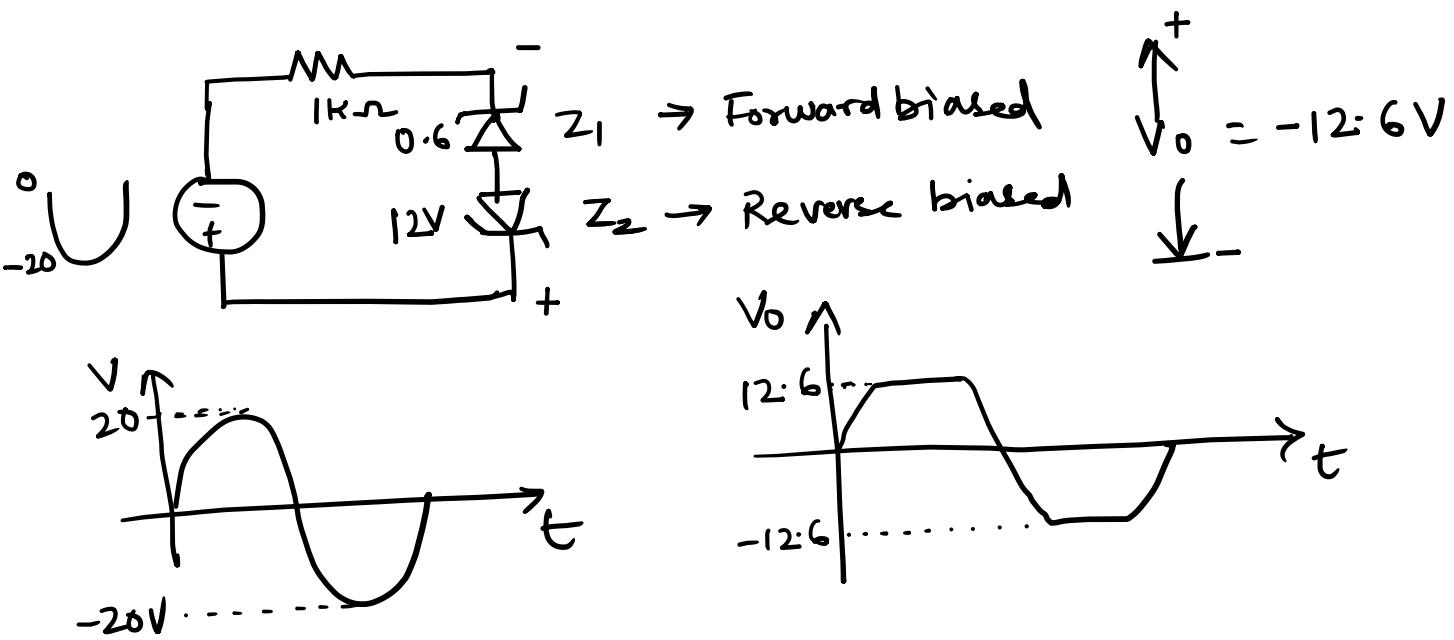
$$I = \frac{26}{1k\Omega} = 26mA$$

Given: $12V \rightarrow \text{Reverse breakdown voltage across } Z_1 \& Z_2$



Given:- Forward bias breakdown voltage = 0.6V
Reverse " " " " = 12V



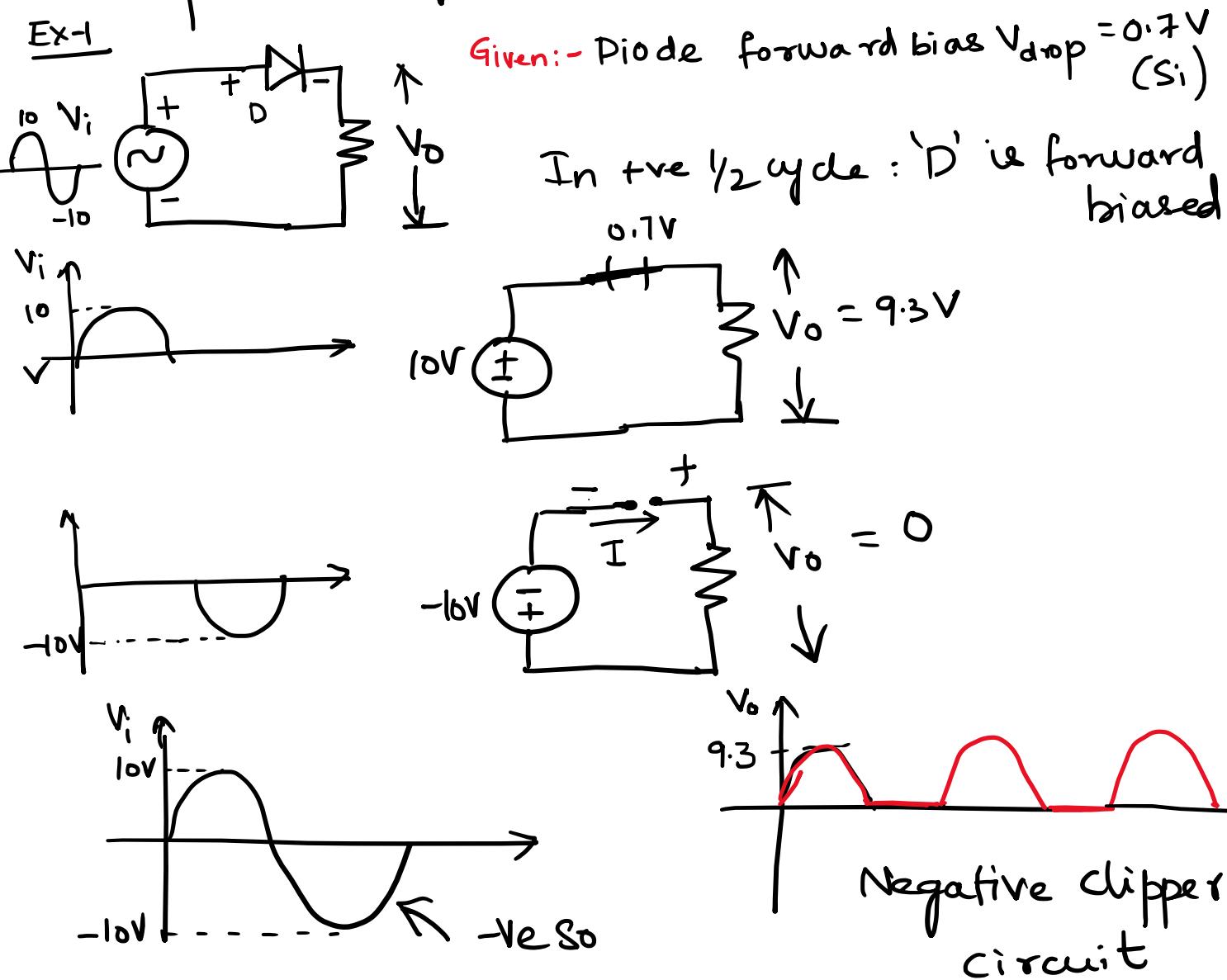


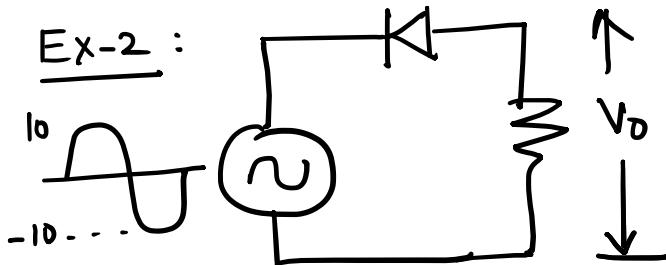
3. Diode Clipper Circuits:

- series
- shunt

Purpose is to clip the unwanted portion of the voltage.

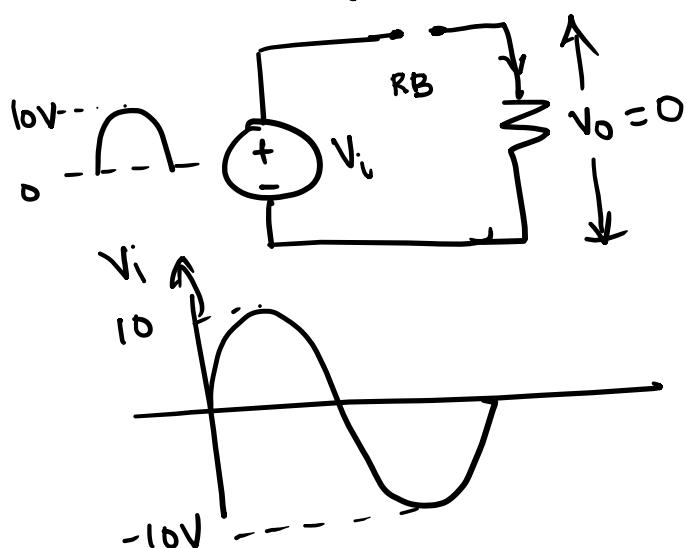
Components required :— Diode, resistor



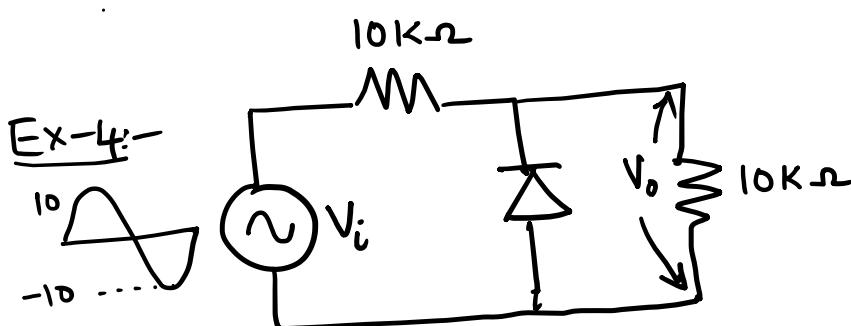
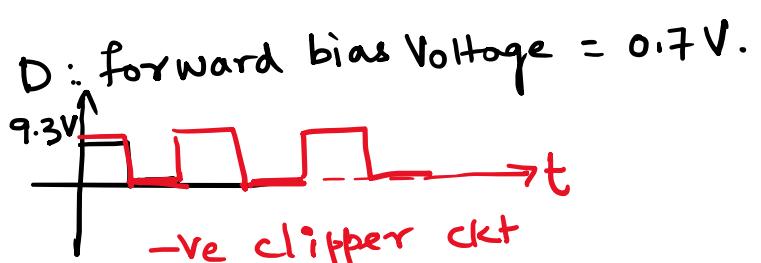
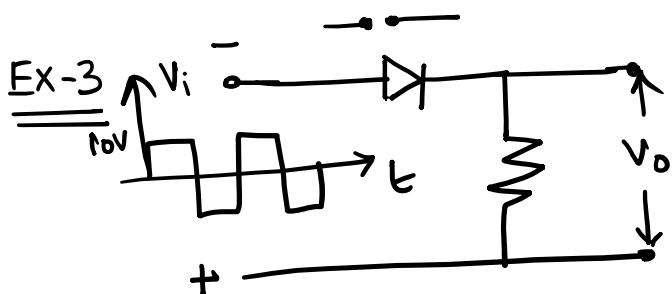
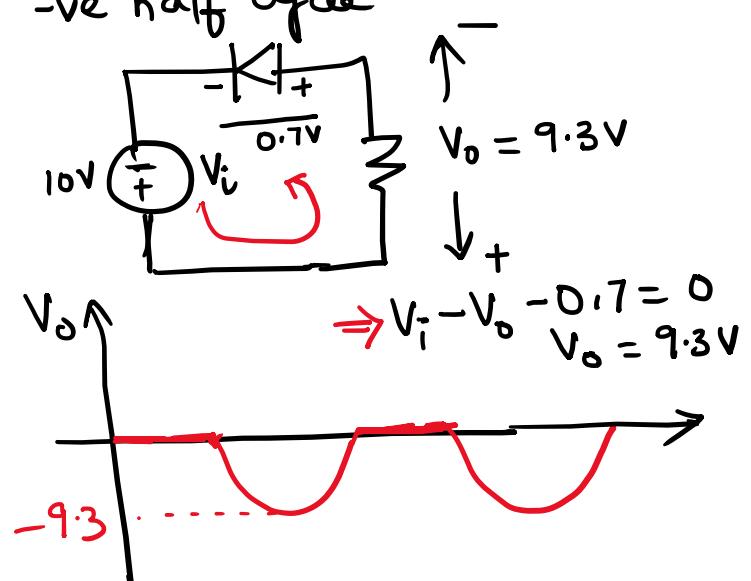


Positive clipper Circuit

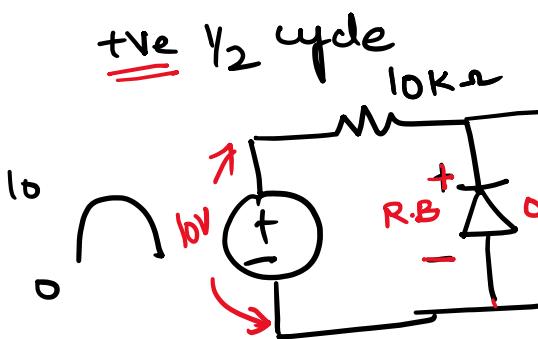
+ve half cycle



-ve half cycle

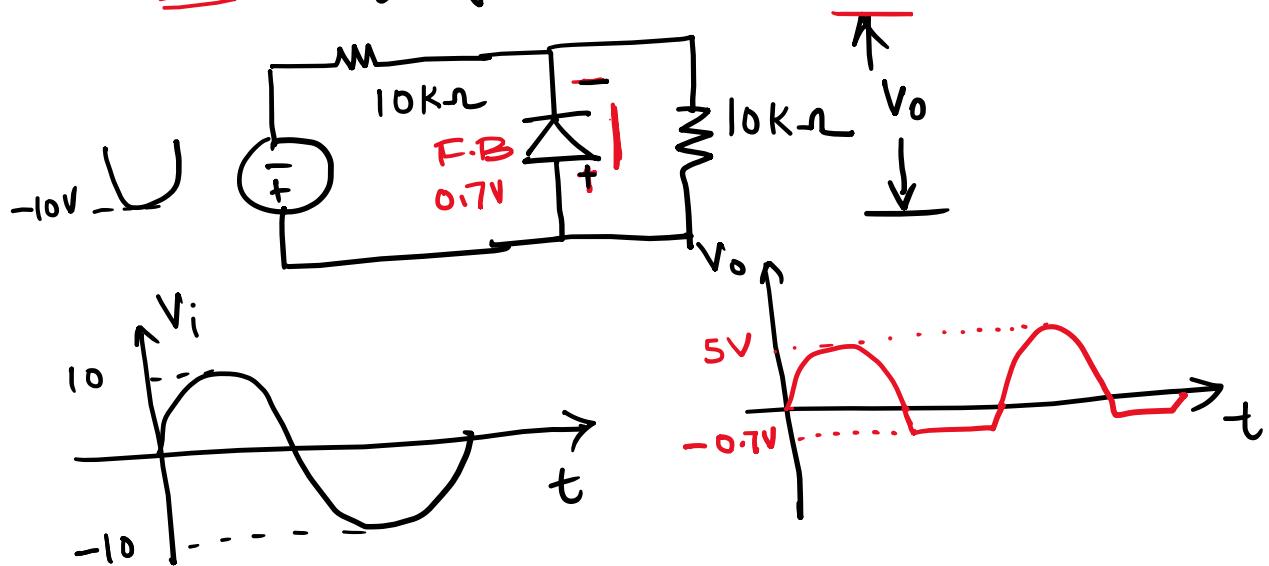


Given: forward bias Diode drop
= 0.7V

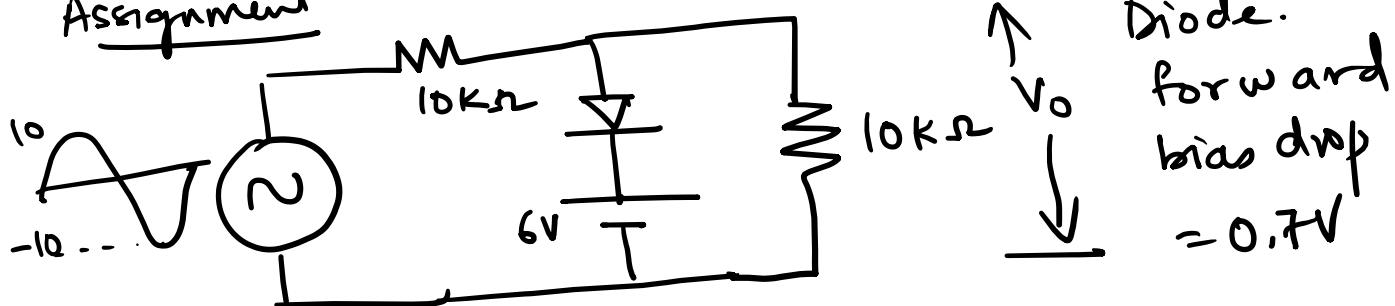


$$V_o = 10V * \left[\frac{10k\Omega}{20k\Omega} \right] = 5V$$

-ve half cycle



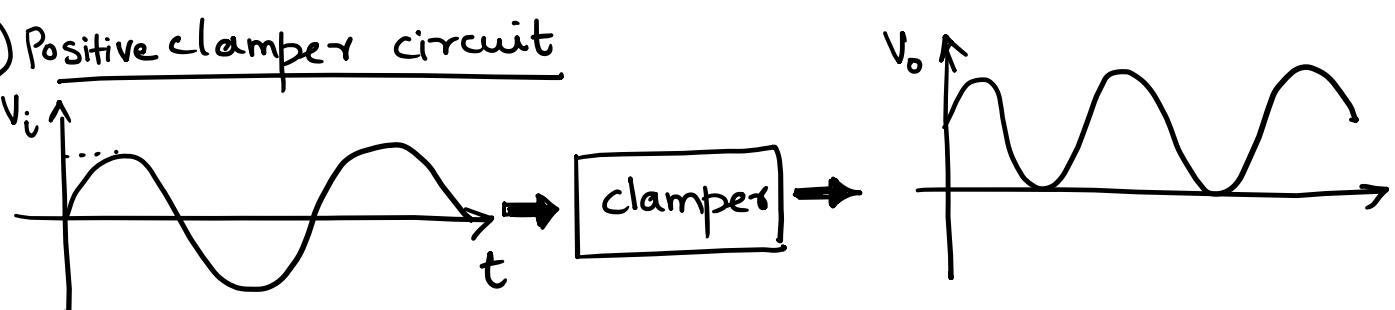
Assignment



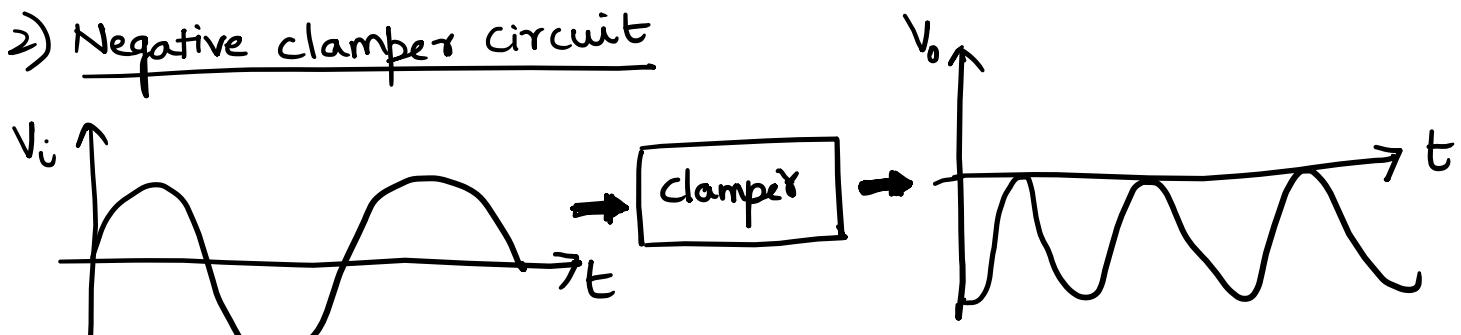
Given :-
Diode.
forward
bias drop
 $= 0.7V$

4. Diode Clamper Circuits: These circuits are designed to change the DC level of the signal, without changing the shape of the signal.

1) Positive clamper circuit

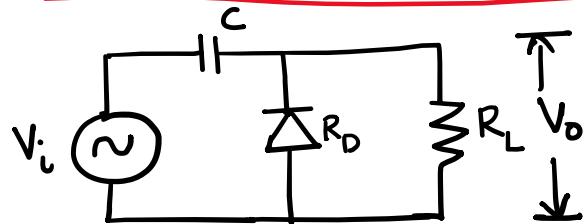


2) Negative clamper circuit

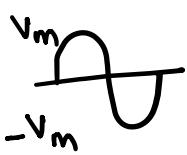


Designed using:- Diode, resistor & capacitor.

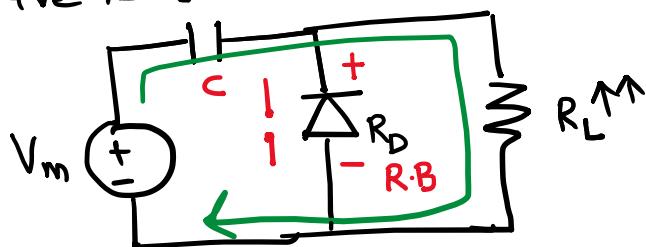
Positive clampper Circuit:



Assumption:- Discharging circuit's time constant ($\tau_d = R_L C$) is much higher than charging circuit's time constant ($\tau_c = R_D C$)



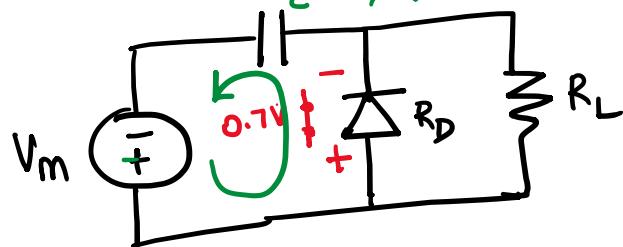
+ve 1/2 cycle:



$$\tau_d = 5 R_L C$$

-ve half cycle

$C \rightarrow$ quicked charged



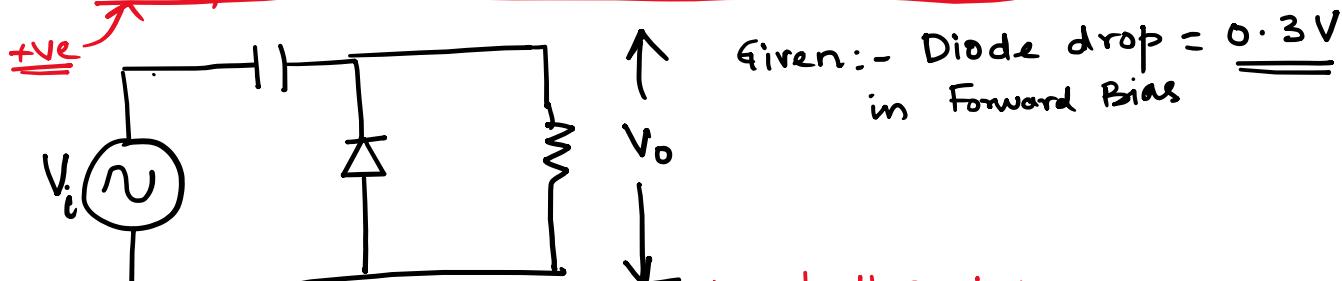
$$\tau_c = 5 R_D C$$

$$\tau_d \ggg \tau_c$$

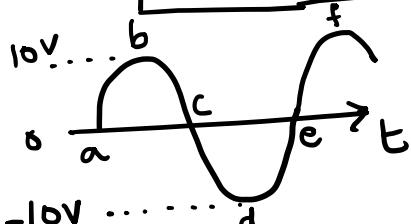
$$5 R_L C \ggg 5 R_D C$$

$$R_L \ggg R_D \Rightarrow R_L = 100 R_D$$

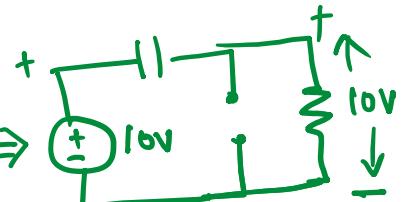
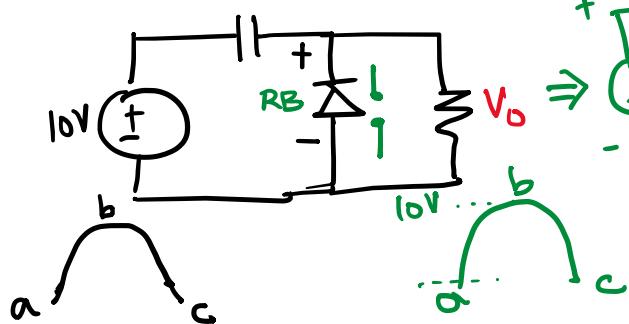
Clamper circuit with Numerical Values



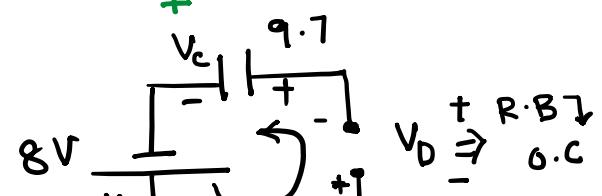
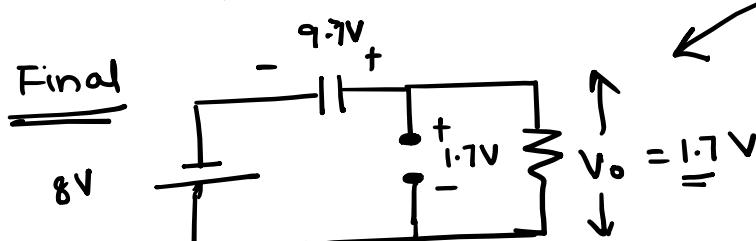
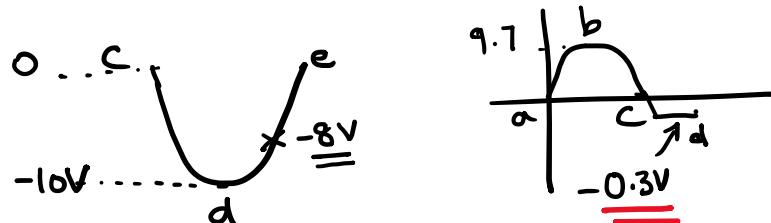
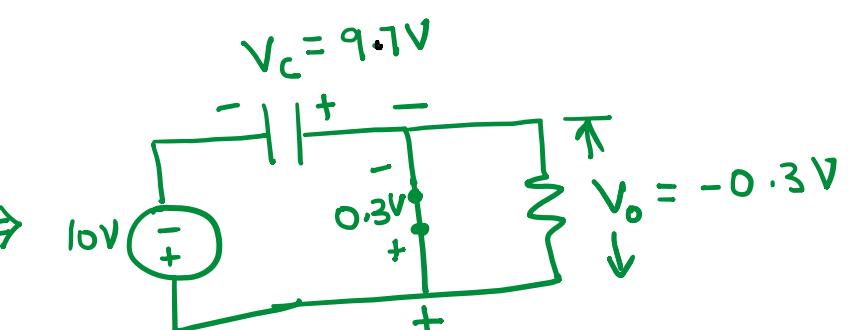
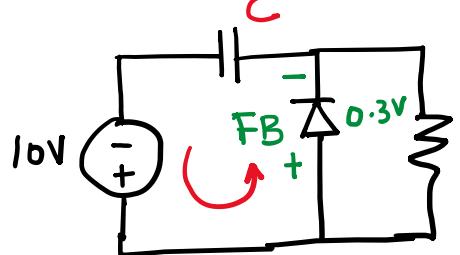
Given:- Diode drop = 0.3V
in Forward Bias



+ve half cycle:-



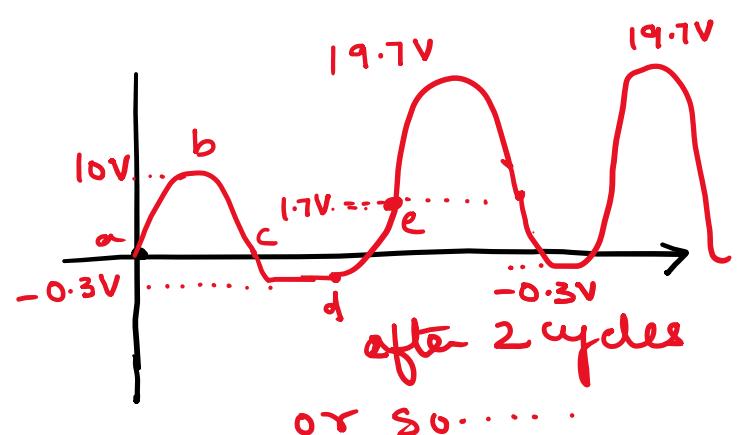
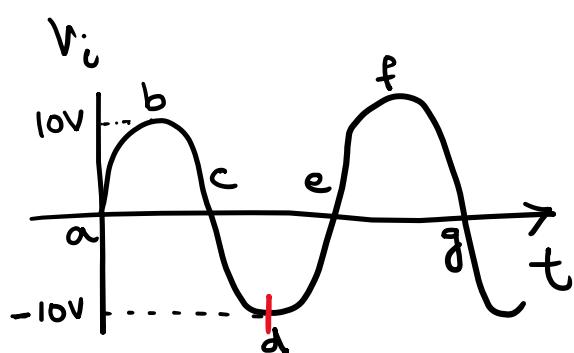
-Ve half cycle



$$V_s - V_D - V_C = 0$$

$$8 - V_D - 9.7 = 0$$

$$V_D = -1.7 \text{ V}$$



-Ve clamper circuit

